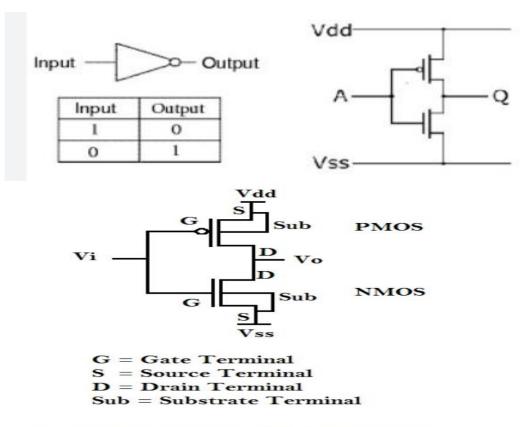
# **CMOS Inverter**

### **INTRODUCTION**

- CMOS stands for "Complementary Metal Oxide Semiconductor".
- Two different types of field-effect transistors: PMOS and NMOS. PMOS transistors use P-type semiconductor materials, while NMOS transistors use N-type semiconductor materials.
- CMOS technology is used for constructing integrated circuit (IC) chips, including microprocessors, microcontrollers, memory chips (including CMOS BIOS), and other digital logic circuits.
- CMOS technology is also used for analog circuits such as image sensors (CMOS sensors), data converters, RF circuits (RF CMOS), and highly integrated transceivers for many types of communication.

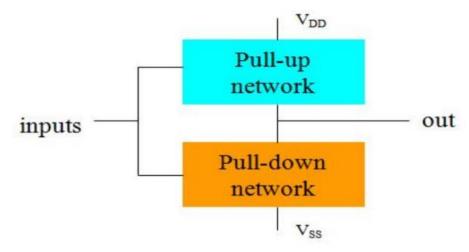
### **CMOS Inverter Schematic Diagram**

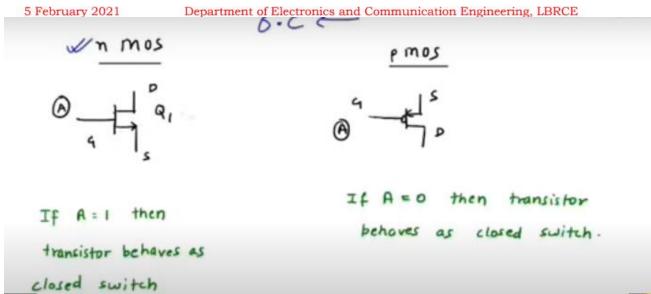


Schematic diagram of CMOS Inverter

# **CMOS Inverter Operation & Working**

Pull-up and pull-down networks:





Given ( $V_{th} = 0.2 V_{dd}$ ), we can analyze the behavior of the transistors under different ( $V_{gs}$ ) conditions.

**NMOS Transistor Behavior** 

1. When the gate-source voltage is less than the threshold voltage, the NMOS transistor is in the cutoff region

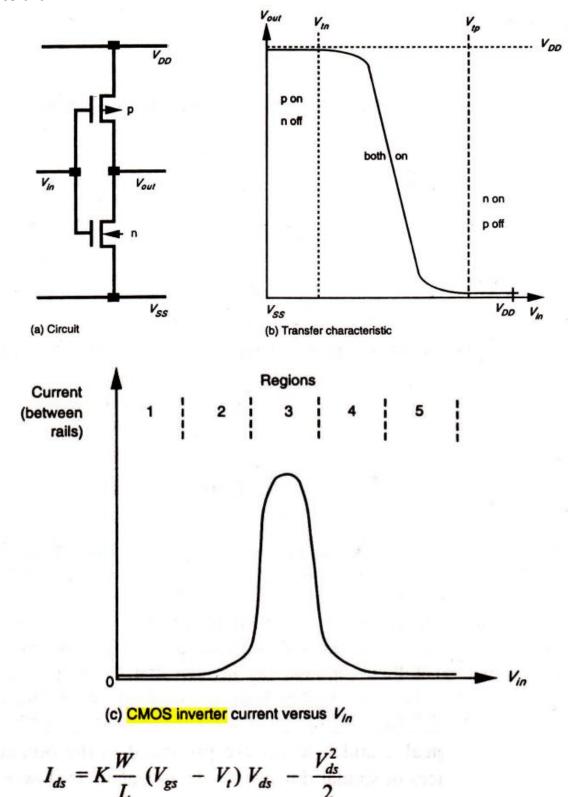
Cutoff Region: The NMOS transistor is OFF, and there is no current flowing from drain to source

- 2. When the gate-source voltage is greater than the threshold voltage, the NMOS transistor is in the active region (also known as the linear or saturation
- -Active Region: The NMOS transistor is ON, and it can conduct current from drain to source.

### **PMOS Transistor Behavior**

- 1. For a PMOS transistor, the gate-source voltage is negative.
- When the magnitude of the gate-source voltage is less than the magnitude of the threshold voltage. the PMOS transistor is in the cutoff region.
- 2. When the magnitude of the gate-source voltage is greater than the magnitude of the threshold voltage., the PMOS transistor is in the active region.

Active Region: The PMOS transistor is ON, and it can conduct current from source to drain..



### **CMOS**

1. 
$$I_{ds} = \frac{(\mu C_0)}{2} \frac{W}{L} (V_{gs} - V_t)^2$$
$$= \frac{\beta}{L} (V_{gs} - V_t)^2 \text{ [In saturation]}$$
with  $|V_{tp}| = 0.2 V_{DD}$ , then

$$\tau_r = \frac{3C_L}{\beta_p V_{DD}}$$

## **Advantages**

# 1. Low Power Consumption:

Static Power: CMOS inverters consume very little power when in a stable state (i.e., when the input is either high or low), as there is minimal current flow through the circuit.

Dynamic Power: During switching, the power consumption is primarily due to the charging and discharging of load capacitances, which is relatively low compared to other technologies.

- 2. High Noise Margin
- 3. High Input Impedance

## **Disadvantages**

- 1. Switching Speed
- 2. Susceptibility to Radiation
- 3. Complexity in Fabrication:
- 4. Subthreshold Leakage:
- 5. Temperature Sensitivity:

## **Applications**

- Logic Gates: Basic building blocks for creating other logic gates like NAND, NOR, etc.
- Ring Oscillators: Used in clock generation circuits.